

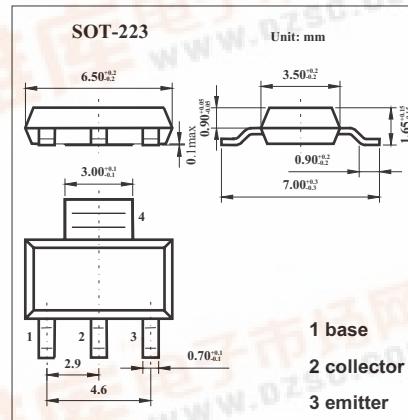
## SMD Type

## Transistors

**NPN Silicon Planar  
Medium Power Transistor  
FZT749**

**■ Features**

- 25 Volt V<sub>CBO</sub>.
- 3 Amp continuous current.
- Low saturation voltage.
- Excellent h<sub>FE</sub> specified up to 6A .

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-35	V
Collector-emitter voltage	V <sub>CBO</sub>	-25	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Continuous collector current	I <sub>CM</sub>	-8	A
Peak pulse current	I <sub>C</sub>	-3	A
Power dissipation	P <sub>tot</sub>	2	W
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to +150	°C

**FZT749**■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Breakdown Voltages	$V_{(\text{BR})\text{CBO}}$	$I_C=-100\mu\text{A}$	-35			V
Breakdown Voltages	$V_{(\text{BR})\text{CEO}}$	$I_C=-10\text{mA}$	-25			V
Breakdown Voltages	$V_{(\text{BR})\text{EBO}}$	$I_E=-100\mu\text{A}$	-5			V
Collector Cut-Off Currents	$I_{\text{CBO}}$	$V_{\text{CB}}=-30\text{V}$ $V_{\text{CB}}=-30\text{V}, T_a = 100^\circ\text{C}$			-0.1 -10	$\mu\text{A}$
Collector Cut-Off Currents	$I_{\text{EBO}}$	$V_{\text{EB}}=4\text{V}$			-0.1	$\mu\text{A}$
Saturation Voltages *	$V_{\text{CE}(\text{sat})}$	$I_C=-1\text{A}, I_B=-100\text{mA}$ $I_C=-3\text{A}, I_B=-300\text{mA}$		-0.12 -0.40	-0.3 -0.6	V
Saturation Voltages *	$V_{\text{BE}(\text{sat})}$	$I_C=-1\text{A}, I_B=-100\text{mA}$		-0.9	-1.25	V
Base-emitter ON voltage *	$V_{\text{BE}(\text{on})}$	$I_C=-1\text{A}, V_{\text{CE}}=-2\text{V}$		-0.8	-1.0	V
Static Forward Current Transfer Ratio	$h_{\text{FE}}$	$I_C=-50\text{mA}, V_{\text{CE}}=-2\text{V}^*$	70	200		
		$I_C=-1\text{A}, V_{\text{CE}}=-2\text{V}^*$	100	200	300	
		$I_C=-2\text{A}, V_{\text{CE}}=-2\text{V}^*$	75	150		
		$I_C=-6\text{A}, V_{\text{CE}}=-2\text{V}^*$	15	50		
Transitional frequency	$f_T$	$I_C=-100\text{mA}, V_{\text{CE}}=-5\text{V}, f=100\text{MHz}$	100	160		MHz
Output capacitance	$C_{\text{obo}}$	$V_{\text{CB}}=-10\text{V}, f=1\text{MHz}$		55	100	pF
Turn-on time	$t_{(\text{on})}$	$I_C=-500\text{mA}, V_{\text{CC}}=-10\text{V}$		40		ns
Turn-off time	$t_{(\text{off})}$	$I_{B1}=I_{B2}=-50\text{mA}$		450		ns

\* Pulse test:  $t_p = 300 \mu\text{s}; d \leq 0.02$ .

## ■ Marking

Marking	FZT749
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